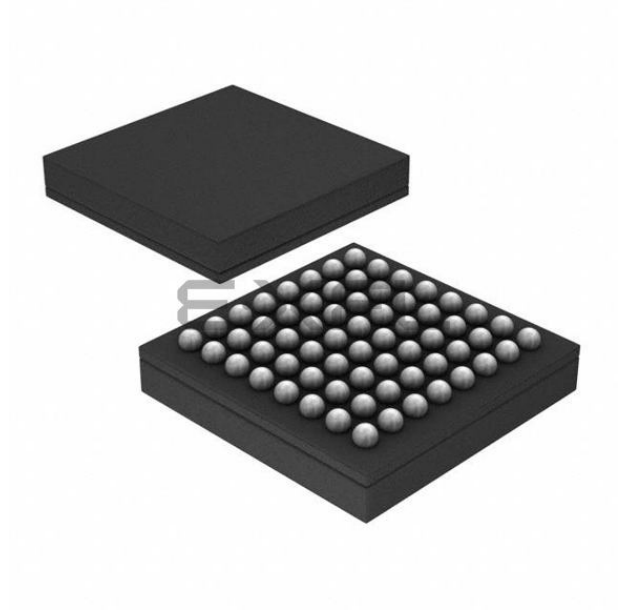


Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, Cap Sense, DMA, I²S, POR, PWM, WDT
Number of I/O	51
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 20x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-TFBGA
Supplier Device Package	64-TFBGA (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l151rbh6a

2 Description

The ultra-low-power STM32L151x6/8/B-A and STM32L152x6/8/B-A devices incorporate the connectivity power of the universal serial bus (USB) with the high-performance ARM® Cortex®-M3 32-bit RISC core operating at a frequency of 32 MHz (33.3 DMIPS), a memory protection unit (MPU), high-speed embedded memories (Flash memory up to 128 Kbytes and RAM up to 32 Kbytes) and an extensive range of enhanced I/Os and peripherals connected to two APB buses.

All the devices offer a 12-bit ADC, 2 DACs and 2 ultra-low-power comparators, six general-purpose 16-bit timers and two basic timers, which can be used as time bases.

Moreover, the STM32L151x6/8/B-A and STM32L152x6/8/B-A devices contain standard and advanced communication interfaces: up to two I^2Cs and SPIs, three USARTs and a USB. The STM32L151x6/8/B-A and STM32L152x6/8/B-A devices offer up to 20 capacitive sensing channels to simply add touch sensing functionality to any application.

They also include a real-time clock with sub-second counting and a set of backup registers that remain powered in Standby mode.

Finally, the integrated LCD controller (except STM32L151x6/8/B-A devices) has a built-in LCD voltage generator that allows to drive up to 8 multiplexed LCDs with contrast independent of the supply voltage.

The ultra-low-power STM32L151x6/8/B-A and STM32L152x6/8/B-A devices operate from a 1.8 to 3.6 V power supply (down to 1.65 V at power down) with BOR and from a 1.65 to 3.6 V power supply without BOR option. They are available in the -40 to +85 °C and -40 to +105°C temperature ranges. A comprehensive set of power-saving modes allows the design of low-power applications.

2.1 Device overview

Table 2. Ultra-low-power STM32L151x6/8/B-A and STM32L152x6/8/B-A device features and peripheral counts

Peripheral		STM32L15xCxxxA			STM32L15xRxxxA			STM32L15xVxxxA	
Flash (Kbytes)		32	64	128	32	64	128	64	128
Data EEPROM (Kbytes)		4							
RAM (Kbytes)		16	32	32	16	32	32	32	32
Timers	General-purpose	6							
	Basic	2							
Communication interfaces	SPI	2							
	I^2C	2							
	USART	3							
	USB	1							
GPIOs		37			51/50(1)			83	
12-bit synchronized ADC Number of channels		1 14 channels			1 20/19 channels(1)			1 24 channels	
12-bit DAC Number of channels		2 2							
LCD (STM32L152xxxxA Only) COM x SEG		4x16			4x32/4x31(1) 8x28/8x27(1)			4x44 8x40	
Comparator		2							
Capacitive sensing channels		13			20				
Max. CPU frequency		32 MHz							
Operating voltage		1.8 V to 3.6 V (down to 1.65 V at power-down) with BOR option 1.65 V to 3.6 V without BOR option							
Operating temperatures		Ambient operating temperatures: –40 to +85 °C / –40 to + 105 °C Junction temperature: -40 to +110°C							
Packages		LQFP48, UFQFPN48			LQFP64, TFBGA64			LQFP100, UFBGA100	

1. For TFBGA64 package (instead of PC3 pin there is V_{REF+} pin).

Table 5. Working mode-dependent functionalities (from Run/active down to standby)

Ips	Run/Active	Sleep	Low-power Run	Low-power Sleep	Stop		Standby	
						Wakeup capability		Wakeup capability
CPU	Y	-	Y	-	-	-	-	-
Flash	Y	Y	Y	Y	-	-	-	-
RAM	Y	Y	Y	Y	Y	-	-	-
Backup Registers	Y	Y	Y	Y	Y	-	Y	-
EEPROM	Y	Y	Y	Y	Y	-	-	-
Brown-out reset (BOR)	Y	Y	Y	Y	Y	Y	Y	-
DMA	Y	Y	Y	Y	-	-	-	-
Programmable Voltage Detector (PVD)	Y	Y	Y	Y	Y	Y	Y	-
Power On Reset (POR)	Y	Y	Y	Y	Y	Y	Y	-
Power Down Rest (PDR)	Y	Y	Y	Y	Y	-	Y	-
High Speed Internal (HSI)	Y	Y	-	-	-	-	-	-
High Speed External (HSE)	Y	Y	-	-	-	-	-	-
Low Speed Internal (LSI)	Y	Y	Y	Y	Y	-	Y	-
Low Speed External (LSE)	Y	Y	Y	Y	Y	-	Y	-
Multi-Speed Internal (MSI)	Y	Y	Y	Y	-	-	-	-
Inter-Connect Controller	Y	Y	Y	Y	-	-	-	-
RTC	Y	Y	Y	Y	Y	Y	Y	-
RTC Tamper	Y	Y	Y	Y	Y	Y	Y	Y
Auto Wakeup (AWU)	Y	Y	Y	Y	Y	Y	Y	Y
LCD	Y	Y	Y	Y	Y	-	-	-
USB	Y	Y	-	-	-	Y	-	-
USART	Y	Y	Y	Y	Y	(1)	-	-
SPI	Y	Y	Y	Y	-	-	-	-
I2C	Y	Y	Y	Y	-	(1)	-	-
ADC	Y	Y	-	-	-	-	-	-

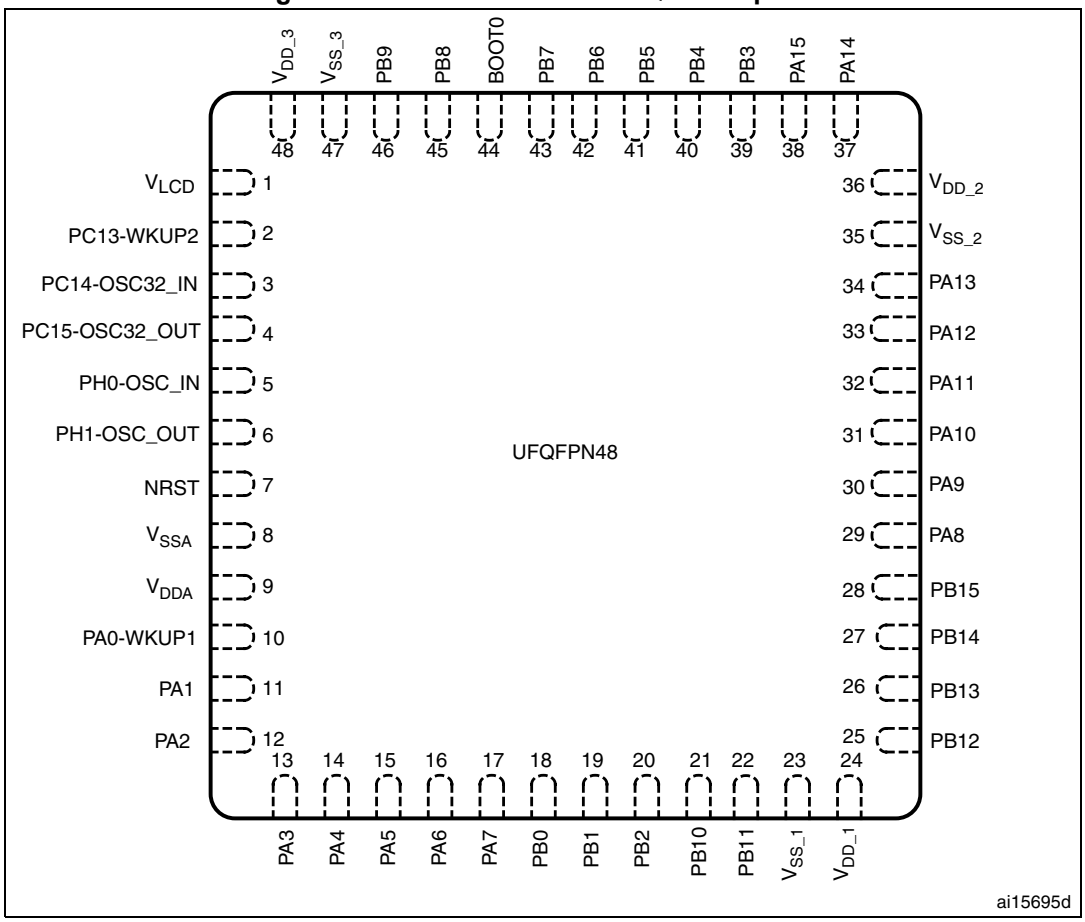
3.4 Clock management

The clock controller distributes the clocks coming from different oscillators to the core and the peripherals. It also manages clock gating for low-power modes and ensures clock robustness. It features:

- **Clock prescaler**: to get the best trade-off between speed and current consumption, the clock frequency to the CPU and peripherals can be adjusted by a programmable prescaler
- **Safe clock switching**: clock sources can be changed safely on the fly in run mode through a configuration register.
- **Clock management**: to reduce power consumption, the clock controller can stop the clock to the core, individual peripherals or memory.
- **Master clock source**: three different clock sources can be used to drive the master clock:
  - 1-24 MHz high-speed external crystal (HSE), that can supply a PLL
  - 16 MHz high-speed internal RC oscillator (HSI), trimmable by software, that can supply a PLL
  - Multispeed internal RC oscillator (MSI), trimmable by software, able to generate 7 frequencies (65.5 kHz, 131 kHz, 262 kHz, 524 kHz, 1.05 MHz, 2.1 MHz, 4.2 MHz) with a consumption proportional to speed, down to 750 nA typical. When a 32.768 kHz clock source is available in the system (LSE), the MSI frequency can be trimmed by software down to a ±0.5% accuracy.
- **Auxiliary clock source**: two ultra-low-power clock sources that can be used to drive the LCD controller and the real-time clock:
  - 32.768 kHz low-speed external crystal (LSE)
  - 37 kHz low-speed internal RC (LSI), also used to drive the independent watchdog. The LSI clock can be measured using the high-speed internal RC oscillator for greater precision.
- **RTC and LCD clock sources:** the LSI, LSE or HSE sources can be chosen to clock the RTC and the LCD, whatever the system clock.
- **USB clock source:** the embedded PLL has a dedicated 48 MHz clock output to supply the USB interface.
- **Startup clock:** after reset, the microcontroller restarts by default with an internal 2.1 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application program as soon as the code execution starts.
- **Clock security system (CSS):** this feature can be enabled by software. If a HSE clock failure occurs, the master clock is automatically switched to HSI and a software interrupt is generated if enabled.
- **Clock-out capability (MCO: microcontroller clock output):** it outputs one of the internal clocks for external use by the application.

Several prescalers allow the configuration of the AHB frequency, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the AHB and the APB domains is 32 MHz. See *Figure 2* for details on the clock tree.

Figure 8. STM32L15xCxxxA UFQFPN48 pinout



1. This figure shows the package top view.

Table 9. STM32L151x6/8/B-A and STM32L152x6/8/B-A pin definitions

Pins					Pin name	Pin type[1]	I/O structure	Main function[2] (after reset)	Pins functions	
LQFP100	LQFP64	TFBGA64	UFBGA100	LQFP48 or UFQFPN48					Alternate functions	Additional functions
1	-	-	B2	-	PE2	I/O	FT	PE2	TRACECLK/ LCD_SEG38/TIM3_ETR	-
2	-	-	A1	-	PE3	I/O	FT	PE3	TRACED0/ LCD_SEG39/TIM3_CH1	-
3	-	-	B1	-	PE4	I/O	FT	PE4	TRACED1/TIM3_CH2	-
4	-	-	C2	-	PE5	I/O	FT	PE5	TRACED2/TIM9_CH1	-
5	-	-	D2	-	PE6-WKUP3	I/O	FT	PE6	TRACED3/TIM9_CH2	WKUP3 /RTC_TAMP3
6	1	B2	E2	1	V_{LCD}[3]	S		V_{LCD}	-	-
7	2	A2	C1	2	PC13-WKUP2	I/O	FT	PC13	-	RTC_TAMP1/ RTC_TS/ RTC_OUT/ WKUP2
8	3	A1	D1	3	PC14-OSC32_IN[4]	I/O	TC	PC14	-	OSC32_IN
9	4	B1	E1	4	PC15-OSC32_OUT[4]	I/O	TC	PC15	-	OSC32_OUT
10	-	-	F2	-	V_{SS_5}	S	-	V_{SS_5}	-	-
11	-	-	G2	-	V_{DD_5}	S	-	V_{DD_5}	-	-
12	5	C1	F1	5	PH0-OSC_IN[5]	I/O	TC	PH0	-	OSC_IN
13	6	D1	G1	6	PH1-OSC_OUT	I/O	TC	PH1	-	OSC_OUT
14	7	E1	H2	7	NRST	I/O	RST	NRST	-	-
15	8	E3	H1	-	PC0	I/O	FT	PC0	LCD_SEG18	ADC_IN10/ COMP1_INP
16	9	E2	J2	-	PC1	I/O	FT	PC1	LCD_SEG19	ADC_IN11/ COMP1_INP
17	10	F2	J3	-	PC2	I/O	FT	PC2	LCD_SEG20	ADC_IN12/ COMP1_INP
18	11	-[6]	K2	-	PC3	I/O	TC	PC3	LCD_SEG21	ADC_IN13/ COMP1_INP
19	12	F1	J1	8	V_{SSA}	S	-	V_{SSA}	-	-

6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 11: Voltage characteristics*, *Table 12: Current characteristics*, and *Table 13: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 11. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
V_{DD}–V_{SS}	External main supply voltage (including V_{DDA} and V_{DD})(1)	–0.3	4.0	V
V_{IN}(2)	Input voltage on five-volt tolerant pin	V_{SS} –0.3	V_{DD}+4.0	
	Input voltage on any other pin	V_{SS} –0.3	4.0	
$\lvert\Delta V_{DDx}\rvert$	Variations between different V_{DD} power pins	-	50	mV
$\lvert V_{SSX} - V_{SS}\rvert$	Variations between all different ground pins(3)	-	50	
V_{REF+} –V_{DDA}	Allowed voltage difference for V_{REF+} > V_{DDA}	-	0.4	V
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see *Section 6.3.11*		-

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. V_{IN} maximum must always be respected. Refer to *Table 12* for maximum allowed injected current values.
3. Include V_{REF-} pin.

Table 12. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI_{VDD}	Total current into sum of all V_{DD_x} power lines (source)(1)	100	mA
ΣI_{VSS}(2)	Total current out of sum of all V_{SS_x} ground lines (sink)(1)	100	
$I_{VDD(PIN)}$	Maximum current into each V_{DD_x} power pin (source)(1)	70	
$I_{VSS(PIN)}$	Maximum current out of each V_{SS_x} ground pin (sink)(1)	-70	
I_{IO}	Output current sunk by any I/O and control pin	25	
	Output current sourced by any I/O and control pin	- 25	
$\Sigma I_{IO(PIN)}$	Total output current sunk by sum of all IOs and control pins(2)	60	
	Total output current sourced by sum of all IOs and control pins(2)	-60	
$I_{INJ(PIN)}$ (3)	Injected current on five-volt tolerant I/O(4) RST and B pins	-5/+0	
	Injected current on any other pin(5)	± 5	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins)(6)	± 25	

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.

Table 25. Peripheral current consumption(1) (continued)

Peripheral		Typical consumption, V_{DD} = 3.0 V, T_A = 25 °C				Unit
		Range 1, V_{CORE}= 1.8 V VOS[1:0] = 01	Range 2, V_{CORE}= 1.5 V VOS[1:0] = 10	Range 3, V_{CORE}= 1.2 V VOS[1:0] = 11	Low-power sleep and run	
$I_{DD\ (RTC)}$		0.4				µA
$I_{DD\ (LCD)}$		3.1				
$I_{DD\ (ADC)}$(4)		1450				
$I_{DD\ (DAC)}$(5)		340				
$I_{DD\ (COMP1)}$		0.16				
$I_{DD\ (COMP2)}$	Slow mode	2				
	Fast mode	5				
$I_{DD\ (PVD / BOR)}$(6)		2.6				
$I_{DD\ (IWDG)}$		0.25				

1. Data based on differential I_{DD} measurement between all peripherals OFF an one peripheral with clock enabled, in the following conditions: f_{HCLK} = 32 MHz (Range 1), f_{HCLK} = 16 MHz (Range 2), f_{HCLK} = 4 MHz (Range 3), f_{HCLK} = 64kHz (Low-power run/sleep), $f_{APB1} = f_{HCLK}$, $f_{APB2} = f_{HCLK}$, default prescaler value for each peripheral. The CPU is in Sleep mode in both cases. No I/O pins toggling.
2. HSI oscillator is OFF for this measure.
3. In low-power sleep and run mode, the Flash memory must always be in power-down mode.
4. Data based on a differential I_{DD} measurement between ADC in reset configuration and continuous ADC conversion (HSI consumption not included).
5. Data based on a differential I_{DD} measurement between DAC in reset configuration and continuous DAC conversion of V_{DD}/2. DAC is in buffered mode, output is left floating.
6. Including supply current of internal reference voltage.

6.3.5 Wakeup time from Low-power mode

The wakeup times given in the following table are measured with the MSI RC oscillator. The clock source used to wake up the device depends on the current operating mode:

- Sleep mode: the clock source is the clock that was set before entering Sleep mode
- Stop mode: the clock source is the MSI oscillator in the range configured before entering Stop mode
- Standby mode: the clock source is the MSI oscillator running at 2.1 MHz

All timings are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

6.3.6 External clock source characteristics

High-speed external user clock generated from an external source

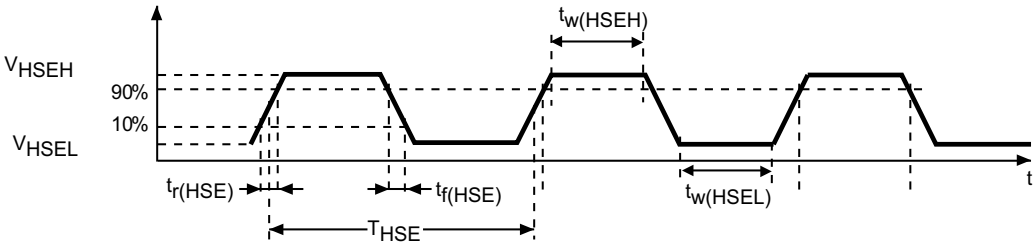
In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO. The external clock signal has to respect the I/O characteristics in *Section 6.3.13*. However, the recommended clock input waveform is shown in *Figure 15*.

Table 27. High-speed external user clock characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency	CSS is on or PLL is used	1	8	32	MHz
		CSS is off, PLL not used	0			
V_{HSEH}	OSC_IN input pin high level voltage	-	$0.7V_{DD}$	-	V_{DD}	
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}		$0.3V_{DD}$	
$t_{w(HSEH)}$ $t_{w(HSEL)}$	OSC_IN high or low time		12	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time		-	-	20	
$C_{in(HSE)}$	OSC_IN input capacitance	-	-	2.6	-	pF

1. Guaranteed by design.

Figure 15. High-speed external clock source AC timing diagram



6.3.7 Internal clock source characteristics

The parameters given in the following table are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

High-speed internal (HSI) RC oscillator

Table 31. HSI oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	V_{DD} = 3.0 V	-	16	-	MHz
$TRIM^{(1)(2)}$	HSI user-trimmed resolution	Trimming code is not a multiple of 16	-	±0.4	0.7	%
		Trimming code is a multiple of 16	-	-	±1.5	%
$ACC_{HSI}^{(2)}$	Accuracy of the factory-calibrated HSI oscillator	V_{DDA} = 3.0 V, T_A = 25 °C	-1(3)	-	1(3)	%
		V_{DDA} = 3.0 V, T_A = 0 to 55 °C	-1.5	-	1.5	%
		V_{DDA} = 3.0 V, T_A = -10 to 70 °C	-2	-	2	%
		V_{DDA} = 3.0 V, T_A = -10 to 85 °C	-2.5	-	2	%
		V_{DDA} = 3.0 V, T_A = -10 to 105 °C	-4	-	2	%
		V_{DDA} = 1.65 V to 3.6 V T_A = -40 to 105 °C	-4	-	3	%
$t_{SU(HSI)}^{(2)}$	HSI oscillator startup time	-	-	3.7	6	µs
$I_{DD(HSI)}^{(2)}$	HSI oscillator power consumption	-	-	100	140	µA

1. The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).
2. Guaranteed by characterization results.
3. Guaranteed by test in production.

Low-speed internal (LSI) RC oscillator

Table 32. LSI oscillator characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$f_{LSI}^{(1)}$	LSI frequency	26	38	56	kHz
$D_{LSI}^{(2)}$	LSI oscillator frequency drift 0°C ≤T_A ≤85°C	-10	-	4	%
$t_{su(LSI)}^{(3)}$	LSI oscillator startup time	-	-	200	µs
$I_{DD(LSI)}^{(3)}$	LSI oscillator power consumption	-	400	510	nA

1. Guaranteed by test in production.
2. This is a deviation for an individual part, once the initial frequency has been measured.
3. Guaranteed by design.

6.3.9 Memory characteristics

The characteristics are given at T_A = -40 to 105 °C unless otherwise specified.

RAM memory

Table 35. RAM and hardware registers

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
VRM	Data retention mode(1)	STOP mode (or RESET)	1.65	-	-	V

1. Minimum supply voltage without losing data stored in RAM (in Stop mode or under Reset) or in hardware registers (only in Stop mode).

Flash memory and data EEPROM

Table 36. Flash memory and data EEPROM characteristics

Symbol	Parameter	Conditions	Min	Typ	Max(1)	Unit
V_{DD}	Operating voltage Read / Write / Erase	-	1.65	-	3.6	V
t_{prog}	Programming / erasing time for byte / word / double word / half-page	Erasing	-	3.28	3.94	ms
		Programming	-	3.28	3.94	
I_{DD}	Average current during whole program/erase operation	T_A = 25 °C, V_{DD} = 3.6 V	-	300	-	µA
	Maximum current (peak) during program/erase operation		-	1.5	2.5	mA

1. Guaranteed by design.

Table 37. Flash memory, data EEPROM endurance and data retention

Symbol	Parameter	Conditions	Value			Unit
			Min(1)	Typ	Max	
NCYC(2)	Cycling (erase / write) Program memory	T_A = -40°C to 105 °C	10	-	-	kcycles
	Cycling (erase / write) EEPROM data memory		300	-	-	
t_{RET}(2)	Data retention (program memory) after 10 kcycles at T_A = 85 °C	TRET = +85 °C	30	-	-	years
	Data retention (EEPROM data memory) after 300 kcycles at T_A = 85 °C		30	-	-	
	Data retention (program memory) after 10 kcycles at T_A = 105 °C	TRET = +105 °C	10	-	-	
	Data retention (EEPROM data memory) after 300 kcycles at T_A = 105 °C		10	-	-	

1. Guaranteed by characterization results.
2. Characterization is done according to JEDEC JESD22-A117.

6.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during the device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 38*. They are based on the EMS levels and classes defined in application note AN1709.

Table 38. EMS characteristics

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, LQFP100, T_A = +25 °C, f_{HCLK} = 32 MHz conforms to IEC 61000-4-2	3B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, LQFP100, T_A = +25 °C, f_{HCLK} = 32 MHz conforms to IEC 61000-4-4	4A

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the oscillator pins for 1 second.

6.3.13 I/O port characteristics

General input/output characteristics

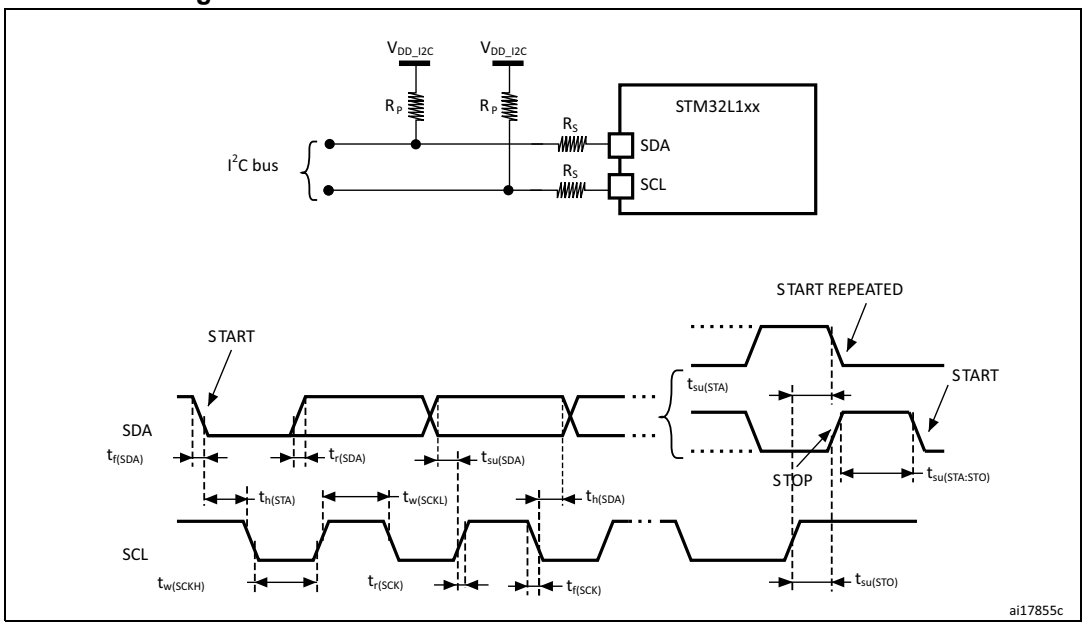
Unless otherwise specified, the parameters given in *Table 43* are derived from tests performed under conditions summarized in *Table 14*. All I/Os are CMOS and TTL compliant.

Table 43. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Input low level voltage	TC and FT I/O	-	-	0.3 V_{DD}(1)(2)	V
		BOOT0	-		0.14 V_{DD}(2)	
V_{IH}	Input high level voltage	TC I/O	0.45 V_{DD}+0.38(2)	-	-	
		FT I/O	0.39 V_{DD}+0.59(2)	-	-	
		BOOT0	0.15 V_{DD}+0.56(2)	-	-	
V_{hys}	I/O Schmitt trigger voltage hysteresis(2)	TC and FT I/O	-	10% V_{DD}(3)	-	
		BOOT0	-	0.01	-	
I_{lkg}	Input leakage current(4)	$V_{SS} \le V_{IN} \le V_{DD}$ I/Os with LCD	-	-	±50	nA
		$V_{SS} \le V_{IN} \le V_{DD}$ I/Os with analog switches	-	-	±50	
		$V_{SS} \le V_{IN} \le V_{DD}$ I/Os with analog switches and LCD	-	-	±50	
		$V_{SS} \le V_{IN} \le V_{DD}$ I/Os with USB	-	-	±250	
		$V_{SS} \le V_{IN} \le V_{DD}$ TC and FT I/O	-	-	±50	
		FT I/O $V_{DD} \le V_{IN} \le 5V$	-	-	±10	uA
R_{PU}	Weak pull-up equivalent resistor(5)(1)	$V_{IN} = V_{SS}$	30	45	60	kΩ
R_{PD}	Weak pull-down equivalent resistor(5)	$V_{IN} = V_{DD}$	30	45	60	kΩ
C_{IO}	I/O pin capacitance	-	-	5	-	pF

1. Guaranteed by test in production.
2. Guaranteed by design.
3. With a minimum of 200 mV.
4. The max. value may be exceeded if negative current is injected on adjacent pins.
5. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimal (~10% order).

Figure 21. I²C bus AC waveforms and measurement circuit



1. R_S = series protection resistors
2. R_P = pull-up resistors
3. V_{DD_I2C} = I2C bus supply
4. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Table 49. SCL frequency (f_{PCLK1}= 32 MHz, V_{DD} = V_{DD_I2C} = 3.3 V)(1)(2)

f_{SCL} (kHz)	I2C_CCR value
	R_P = 4.7 kΩ
400	0x801B
300	0x8024
200	0x8035
100	0x00A0
50	0x0140
20	0x0320

1. R_P = External pull-up resistance, f_{SCL} = I²C speed.
2. For speeds around 200 kHz, the tolerance on the achieved speed is ±5%. For other speed ranges, the tolerance on the achieved speed is ±2%. These variations depend on the accuracy of the external components used to design the application.

6.3.18 DAC electrical specifications

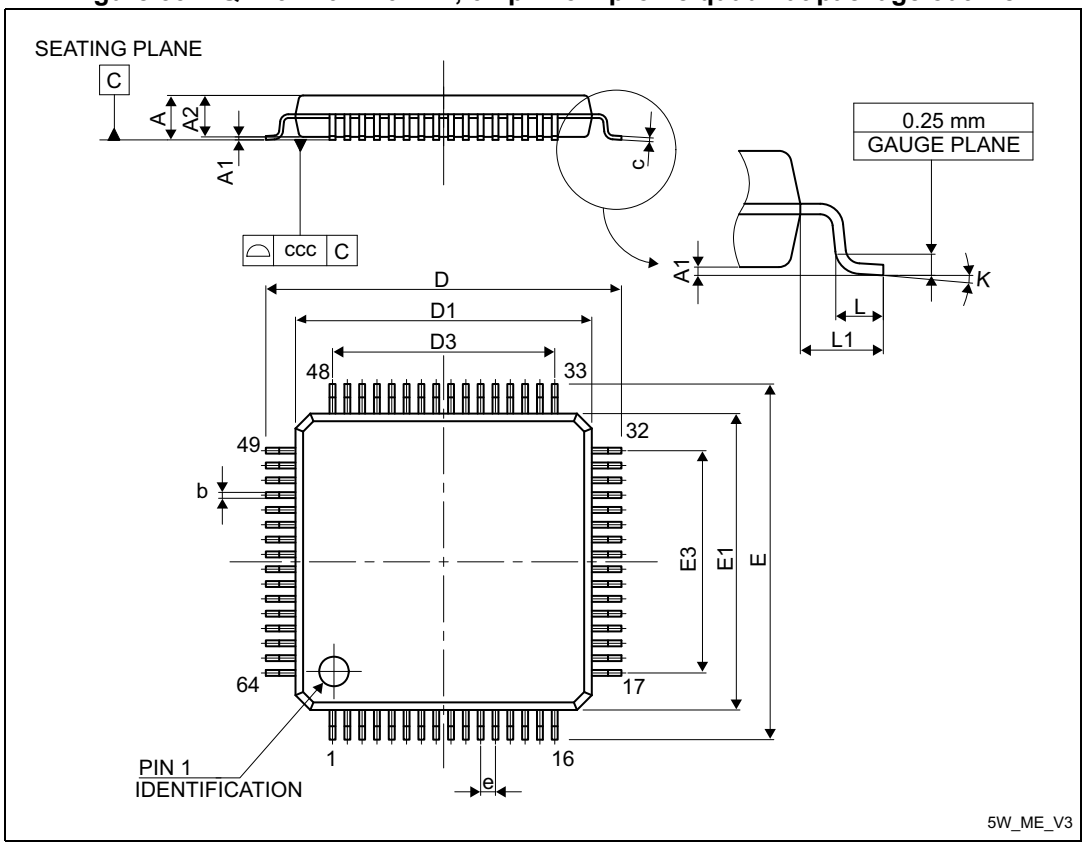
Data guaranteed by design, unless otherwise specified.

Table 58. DAC characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage	-		1.8	-	3.6	V
V_{REF+}	Reference supply voltage	V_{REF+} must always be below V_{DDA}		1.8	-	3.6	V
V_{REF-}	Lower reference voltage	-		V_{SSA}			V
$I_{DDVREF+}$(1)	Current consumption on V_{REF+} supply V_{REF+} = 3.3 V	No load, middle code (0x800)		-	130	220	µA
		No load, worst code (0x000)		-	220	350	µA
I_{DDA}(1)	Current consumption on V_{DDA} supply V_{DDA} = 3.3 V	No load, middle code (0x800)		-	210	320	µA
		No load, worst code (0xF1C)		-	320	520	µA
R_L	Resistive load	DAC output buffer ON	Connected to V_{SSA}	5	-	-	kΩ
			Connected to V_{DDA}	25	-	-	
C_L	Capacitive load	DAC output buffer ON		-	-	50	pF
R_O	Output impedance	DAC output buffer OFF		12	16	20	kΩ
V_{DAC_OUT}	Voltage on DAC_OUT output	DAC output buffer ON		0.2	-	V_{DDA} – 0.2	V
		DAC output buffer OFF		0.5	-	V_{REF+}– 1LSB	mV
DNL(1)	Differential non linearity(2)	$C_L \leq 50$ pF, $R_L \geq 5$ kΩ DAC output buffer ON		-	1.5	3	LSB
		No R_L, $C_L \leq 50$ pF DAC output buffer OFF		-	1.5	3	
INL(1)	Integral non linearity(3)	$C_L \leq 50$ pF, $R_L \geq 5$ kΩ DAC output buffer ON		-	2	4	
		No R_L, $C_L \leq 50$ pF DAC output buffer OFF		-	2	4	
Offset(1)	Offset error at code 0x800 (4)	$C_L \leq 50$ pF, $R_L \geq 5$ kΩ DAC output buffer ON		-	±10	±25	
		No R_L, $C_L \leq 50$ pF DAC output buffer OFF		-	±5	±8	
Offset1(1)	Offset error at code 0x001(5)	No R_L, $C_L \leq 50$ pF DAC output buffer OFF		-	±1.5	±5	

7.2 LQFP64 10 x 10 mm, 64-pin low-profile quad flat package information

Figure 33. LQFP64 10 x 10 mm, 64-pin low-profile quad flat package outline



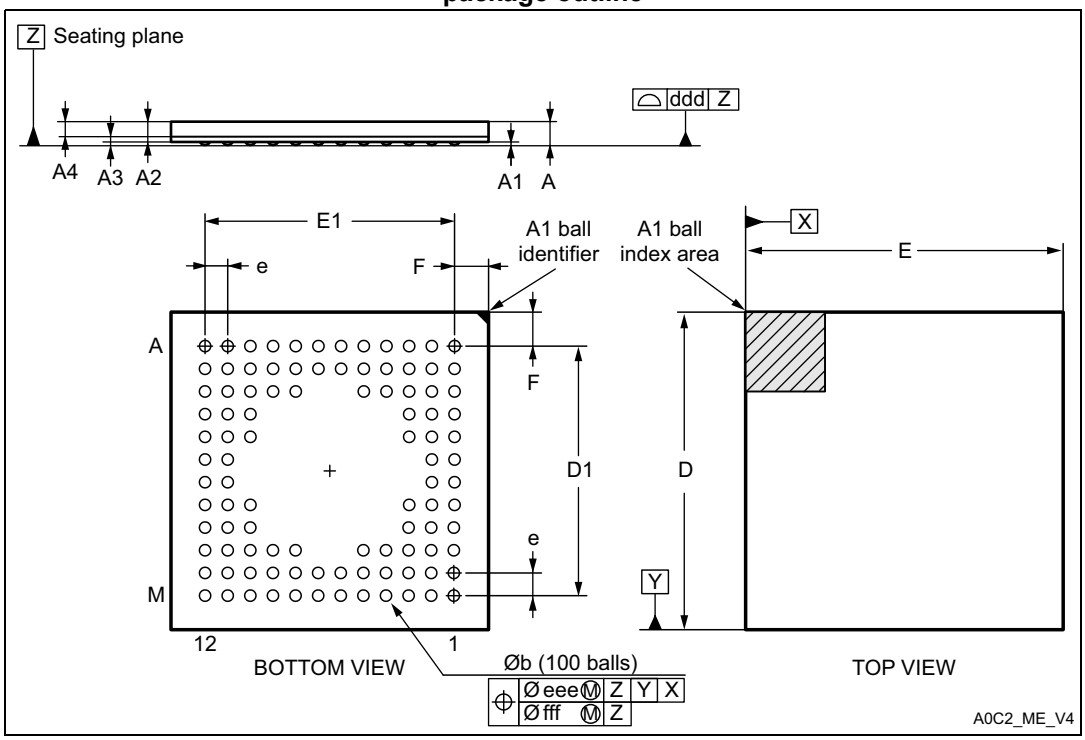
1. Drawing is not to scale.

Table 65. LQFP64 10 x 10 mm, 64-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Typ	Min	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-

7.5 UFBGA100 7 x 7 mm, 0.5 mm pitch, ultra thin fine-pitch ball grid array package information

Figure 42. UFBGA100, 7 x 7 mm, 0.5 mm pitch, ultra thin fine-pitch ball grid array package outline



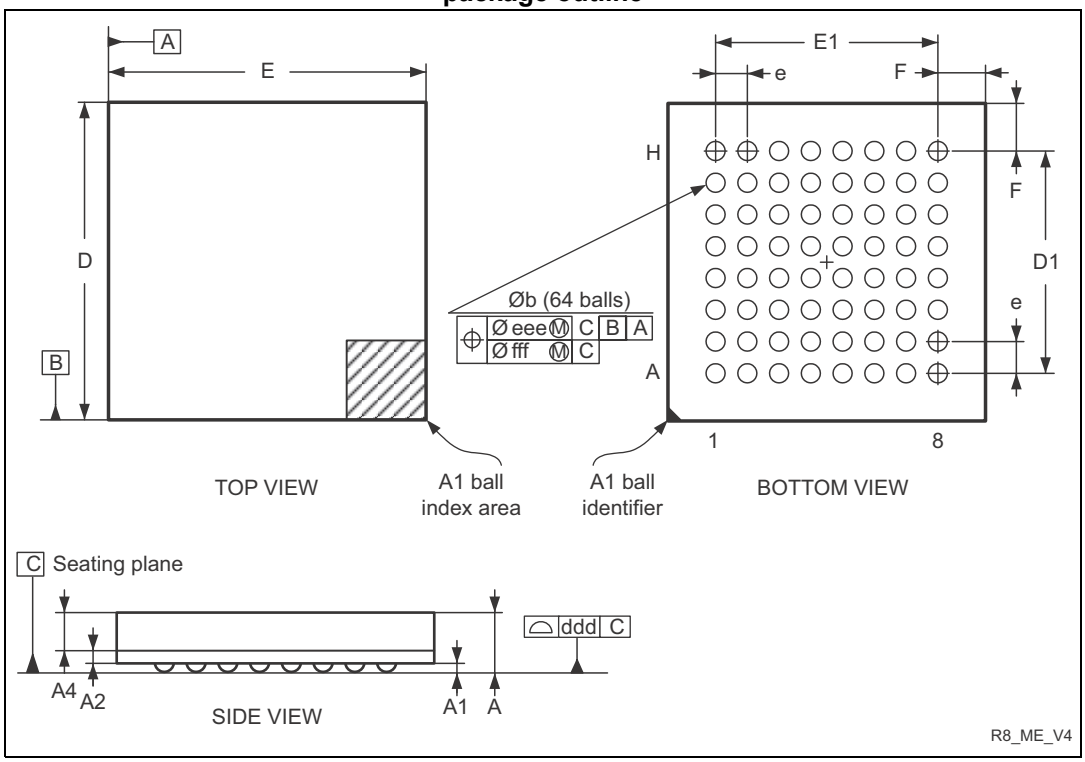
1. Drawing is not to scale.

Table 68. UFBGA100 7 x 7 mm, 0.5 mm pitch, ultra thin fine-pitch ball grid array package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	0.6	-	-	0.0236
A1	0.05	0.08	0.11	0.002	0.0031	0.0043
A2	0.4	0.45	0.5	0.0157	0.0177	0.0197
A3	0.08	0.13	0.18	0.0031	0.0051	0.0071
A4	0.27	0.32	0.37	0.0106	0.0126	0.0146
b	0.2	0.25	0.3	0.0079	0.0098	0.0118
D	6.95	7	7.05	0.2736	0.2756	0.2776
D1	5.45	5.5	5.55	0.2146	0.2165	0.2185
E	6.95	7	7.05	0.2736	0.2756	0.2776
E1	5.45	5.5	5.55	0.2146	0.2165	0.2185
e	-	0.5	-	-	0.0197	-

7.6 TFBGA64 5 x 5 mm, 0.5 mm pitch, thin fine-pitch ball grid array package information

Figure 45. TFBGA64 5 x 5 mm, 0.5 mm pitch, thin fine-pitch ball grid array package outline



1. Drawing is not to scale.

Table 70. TFBGA64 5 x 5 mm, 0.5 mm pitch, thin fine-pitch ball grid array package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.200	-	-	0.0472
A1	0.150	-	-	0.0059	-	-
A2	-	0.200	-	-	0.0079	-
A4	-	-	0.600	-	-	0.0236
b	0.250	0.300	0.350	0.0098	0.0118	0.0138
D	4.850	5.000	5.150	0.1909	0.1969	0.2028
D1	-	3.500	-	-	0.1378	-
E	4.850	5.000	5.150	0.1909	0.1969	0.2028
E1	-	3.500	-	-	0.1378	-
e	-	0.500	-	-	0.0197	-
F	-	0.750	-	-	0.0295	-

9 Revision history

Table 74. Document revision history

Date	Revision	Changes
04-Feb-2014	1	Initial release.
12-Mar-2014	2	Updated *Section 3.5: Low-power real-time clock and backup registers*, *Section 6.1.2: Typical values* and *Section 6.3.4: Supply current characteristics*. Updated *General PCB design guidelines*. Updated *Table 5: Working mode-dependent functionalities (from Run/active down to standby)*, *Table 14: General operating conditions*, *Table 21: Current consumption in Low-power run mode*, *Table 22: Current consumption in Low-power sleep mode*, *Table 23: Typical and maximum current consumptions in Stop mode*, *Table 24: Typical and maximum current consumptions in Standby mode*, *Table 25: Peripheral current consumption*, *Table 42: I/O current injection susceptibility*, *Table 66: I/O static characteristics* and *Table 46: NRST pin characteristics*. Updated *Figure 14: Current consumption measurement scheme*.
04-Feb-2015	3	Updated DMIPS features in cover page and *Section 2: Description*. Updated max temperature at 105°C instead of 85°C in the whole datasheet. Updated current consumption in *Table 20: Current consumption in Sleep mode*. Updated *Table 25: Peripheral current consumption* with new measured values. Updated *Table 57: Maximum source impedance RAIN max* adding note 2. Updated *Section 7: Package information* with new package device marking. Updated *Figure 9: Memory map*.